



Product Overview

MBRD1035CTL: Schottky Power Rectifier, Switch-mode, 10 A, 35 V

For complete documentation, see the data sheet

Product Description

The Schottky Rectifier employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for use as rectifiers in low voltage, high frequency inverters, free wheeling diodes and polarity protection diodes.

Features

- Highly Stable Oxide Passivated Junction
- Guardring for Stress Protection
- Matched dual die construction - May be Paralleled for High Current Output
- High dv/dt Capability
- Short Heat Sink Tap Manufactured - Not Sheared
- Very Low Forward Voltage Drop
- Epoxy Meets UL94, VO at 1/8"

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 0.4 gram (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable

Part Electrical Specifications

Product	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (uA)	$I_{O(rec)}$ Max (A)	I_{FSM} Max (A)	t_{rr} Max (ns)	C_j Max (pF)	Package Type
MBRD1035CTLG	Pb-free	Active	Common Cathode	35	0.56	2000	10	50	-	-	DPAK-3
	Halide free										
MBRD1035CTLT4G	Pb-free	Active	Common Cathode	35	0.56	2000	10	50	-	-	DPAK-3
	Halide free										
SBRD81035CTLT4G	AEC Qualified	Active	Common Cathode	35	0.56	2000	10	50	-	-	DPAK-3
	PPAP Capable										
	Pb-free										
	Halide free										

For more information please contact your local sales support at www.onsemi.com

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